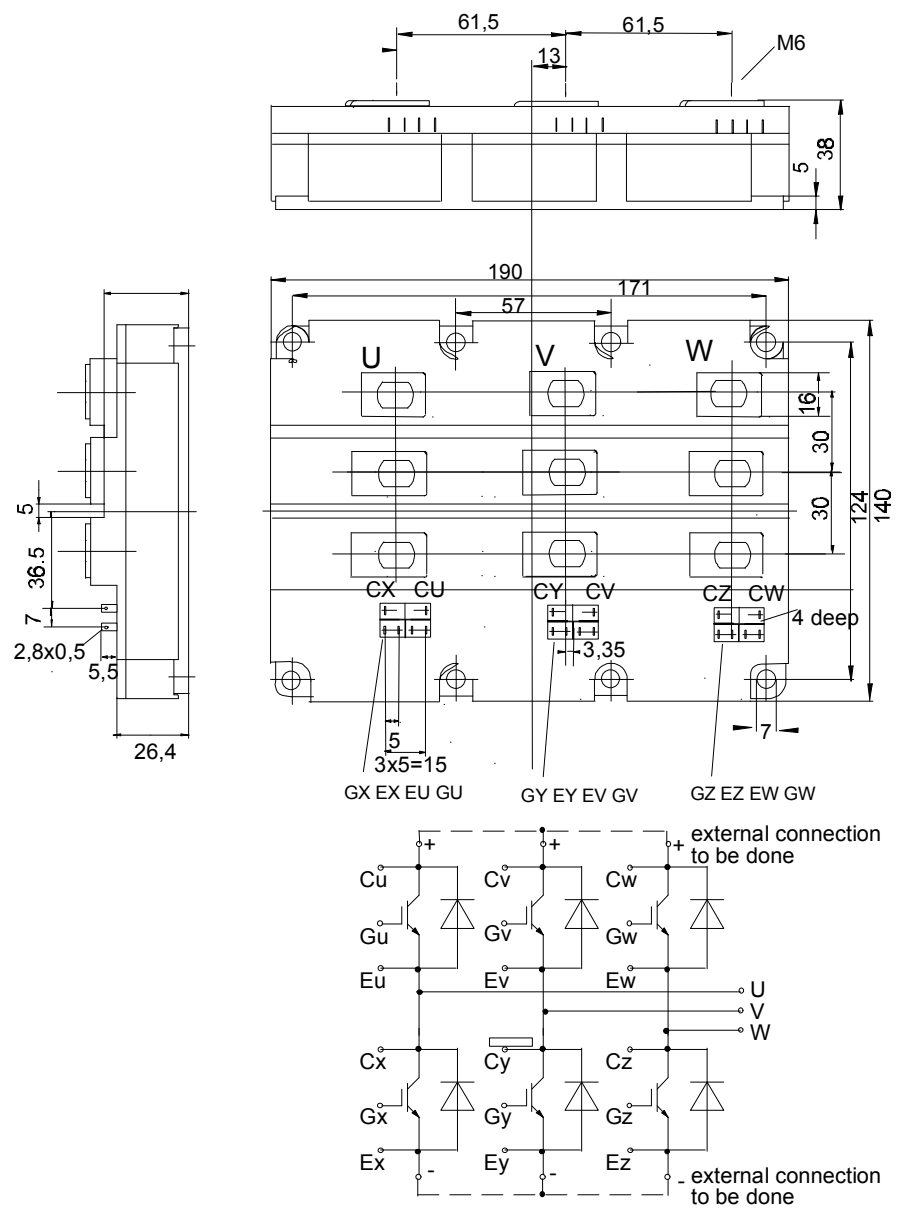




European Power-Semiconductor and Electronics Company GmbH + Co. KG

# Marketing Information

## FS 300 R 16 KF4



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## Höchstzulässige Werte / Maximum rated values

### Elektrische Eigenschaften / Electrical properties

Kollektor-Emitter-Sperrspannung	collector-emitter voltage		$V_{CES}$	1600 V
Kollektor-Dauergleichstrom	DC-collector current		$I_C$	300 A
Periodischer Kollektor Spitzenstrom	repetitive peak collector current	$t_p=1\text{ ms}$	$I_{CRM}$	600 A
Gesamt-Verlustleistung	total power dissipation	$t_c=25^\circ\text{C}$ , Transistor /transistor	$P_{tot}$	2000 W
Gate-Emitter-Spitzenspannung	gate-emitter peak voltage		$V_{GE}$	+/- 20 V
Dauergleichstrom	DC forward current		$I_F$	300 A
Periodischer Spitzenstrom	repetitive peak forw. current	$t_p=1\text{ms}$	$I_{FRM}$	600 A
Isolations-Prüfspannung	insulating test voltage	RMS, f=50 Hz, t= 1 min.	$V_{ISOL}$	3,4 kV

### Charakteristische Werte / Characteristic values: Transistor

				min.	typ.	max
Kollektor-Emitter Sättigungsspannung	collector-emitter saturation voltage	$i_C=300\text{A}, v_{GE}=15\text{V}, t_{vj}=25^\circ\text{C}$	$V_{CE\text{ sat}}$	-	3,5	3,9 V
		$i_C=300\text{A}, v_{GE}=15\text{V}, t_{vj}=125^\circ\text{C}$		-	4,6	5,0 V
Gate-Schwelspannung	gate threshold voltage	$i_C=20\text{mA}, v_{CE}=v_{GE}, t_{vj}=25^\circ\text{C}$	$V_{GE(th)}$	4,5	5,5	6,5 V
Eingangskapazität	input capacity	$f_O=1\text{MHz}, t_{vj}=25^\circ\text{C}, v_{CE}=25\text{V}, v_{GE}=0$	$C_{ies}$	-	45	- nF
Kollektor-Emitter Reststrom	collector-emitter cut-off current	$v_{CE}=1600\text{V}, v_{GE}=0\text{V}, t_{vj}=25^\circ\text{C}$	$i_{CES}$	-	2	- mA
		$v_{CE}=1600\text{V}, v_{GE}=0\text{V}, t_{vj}=125^\circ\text{C}$		-	20	- mA
Gate-Emitter Reststrom	gate leakage current	$v_{CE}=0\text{V}, v_{GE}=20\text{V}, t_{vj}=25^\circ\text{C}$	$i_{GES}$	-	40	400 nA
Emitter-Gate Reststrom	gate leakage current	$v_{CE}=0\text{V}, v_{GE}=20\text{V}, t_{vj}=25^\circ\text{C}$	$i_{GES}$	-	40	400 nA
Einschaltzeit (ohmsche Last)	turn-on time (resistive load)	$i_C=300\text{A}, v_{CE}=900\text{V}, v_{LF}=15\text{V}$	$t_{on}$	-	0,8	- $\mu\text{s}$
		$v_{LR}=15\text{V}, R_G=6,8\ \Omega, t_{vj}=25^\circ\text{C}$		-	1,0	- $\mu\text{s}$
Speicherzeit (induktive Last)	storage time (inductive load)	$i_C=300\text{A}, v_{CE}=900\text{V}, v_{LF}=15\text{V}$	$t_s$	-	1,1	- $\mu\text{s}$
		$v_{LR}=15\text{V}, R_G=6,8\ \Omega, t_{vj}=25^\circ\text{C}$		-	1,3	- $\mu\text{s}$
Fallzeit (induktive Last)	fall time (inductive load)	$i_C=300\text{A}, v_{CE}=900\text{V}, v_{LF}=15\text{V}$	$t_f$	-	0,25	- $\mu\text{s}$
		$v_{LR}=15\text{V}, R_G=6,8\ \Omega, t_{vj}=25^\circ\text{C}$		-	0,30	- $\mu\text{s}$

### Charakteristische Werte / Characteristic values: Invers-Diode

Durchlaßspannung	forward voltage	$i_F=300\text{A}, v_{GE}=0\text{V}, t_{vj}=25^\circ\text{C}$	$V_F$	-	2,4	2,8 V
		$i_F=300\text{A}, v_{GE}=0\text{V}, t_{vj}=125^\circ\text{C}$		-	2,2	- V
Rückstromspitze	peak reverse recovery current	$i_F=300\text{A}, -di_F/dt=300\text{A}/\mu\text{s}$	$I_{RM}$	-	25	- A
		$v_{RM}=900\text{V}, v_{EG}=10\text{V}, t_{vj}=25^\circ\text{C}$		-	50	- A
Sperrverzögerungsladung	recovered charge	$i_F=300\text{A}, -di_F/dt=300\text{A}/\mu\text{s}$	$Q_r$	-	8	- $\mu\text{As}$
		$v_{RM}=900\text{V}, v_{EG}=10\text{V}, t_{vj}=25^\circ\text{C}$		-	30	- $\mu\text{As}$

### Thermische Eigenschaften / Thermal properties

Innerer Wärmewiderstand	thermal resistance, junction to case	Transistor, DC, pro Modul/per module	$R_{thJC}$	0,011 $^\circ\text{C}/\text{W}$
		Transistor, DC, pro Zweig/per arm		0,064 $^\circ\text{C}/\text{W}$
		Diode, DC, pro Modul/per module		0,027 $^\circ\text{C}/\text{W}$
		Diode, DC, pro Zweig/per arm		0,160 $^\circ\text{C}/\text{W}$
Übergangs-Wärmewiderstand	thermal resistance, case to heatsink	pro Module / per Module pro Zweig / per arm	$R_{thCK}$	typ. 0,008 $^\circ\text{C}/\text{W}$ typ. 0,048 $^\circ\text{C}/\text{W}$
Höchstzul. Sperrschichttemperatur	max. junction temperature	pro Module / per Module	$t_{vj\text{ max}}$	150 $^\circ\text{C}$
Betriebstemperatur	operating temperature	Transistor / transistor	$t_{c\text{ op}}$	-40...+150 $^\circ\text{C}$
		Diode / diode	$t_{c\text{ op}}$	-40...+125 $^\circ\text{C}$
Lagertemperatur	storage temperature		$t_{stg}$	-40...+125 $^\circ\text{C}$

### Mechanische Eigenschaften / Mechanical properties

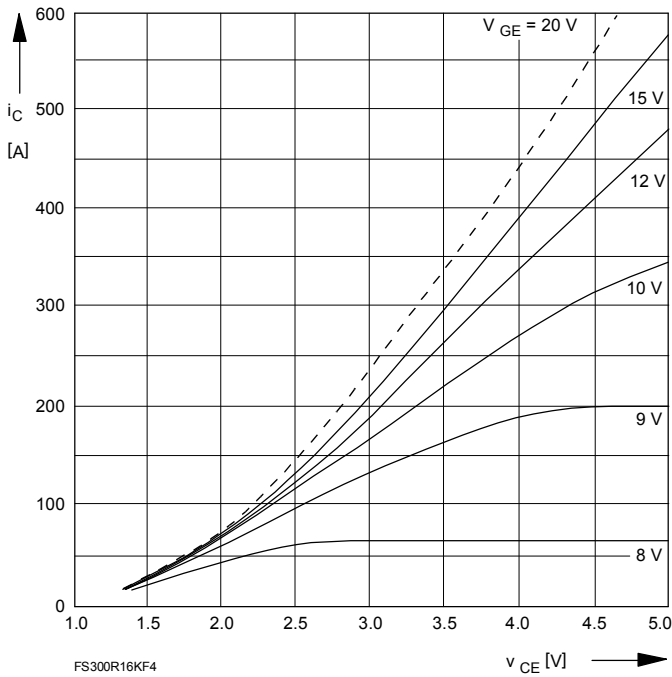
Gehäuse, siehe Anlage	case, see appendix			Seite 1
Innere Isolation	internal insulation			$\text{Al}_2\text{O}_3$
Anzugsdrehmoment f. mech. Befestigung	mounting torque		M1	3 Nm
Anzugsdrehmoment f. elektr. Anschlüsse	terminal connection torque	terminals M6	M2	5...6 Nm
Gewicht	weight		G	ca.2300 g

### Bedingungen für den Kurzschlußschutz

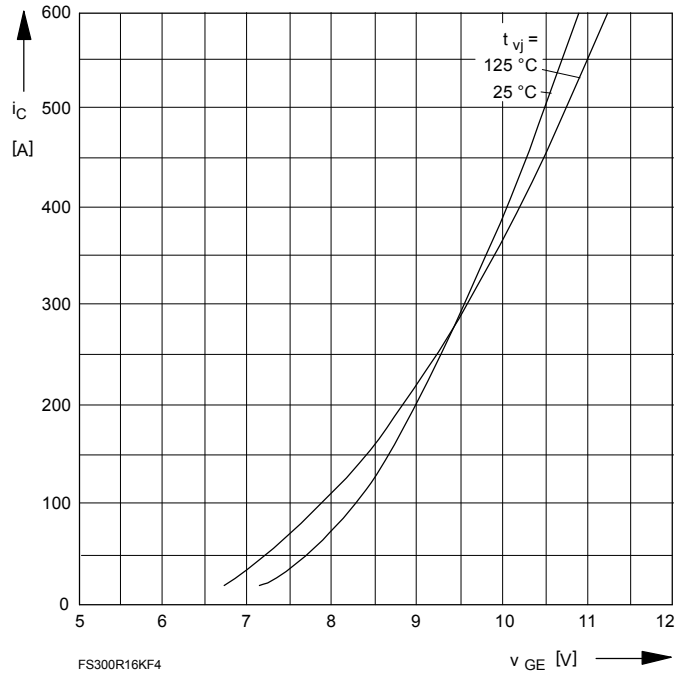
$t_{f0}=10\ \mu\text{s}, v_{LF}=v_{LR}=15\text{V},$	$V_{CC}=1000\text{V}$	Conditions for short-circuit protection
$R_{GF}=R_{GR}=6,8\ \Omega$	$V_{CEM}=1300\text{V}$	Unabhängig davon gilt bei abweich. Bedingungen / with regard to other conditions
$t_{vj}=125^\circ\text{C}$	$i_{CMK1} \gg 3000\text{A}$	$V_{CEM} = V_{CES} -50\text{ nH} \times I_{diC}/dt$
	$i_{CMK2} \gg 2300\text{A}$	

Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen. This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the relevant technical notes.

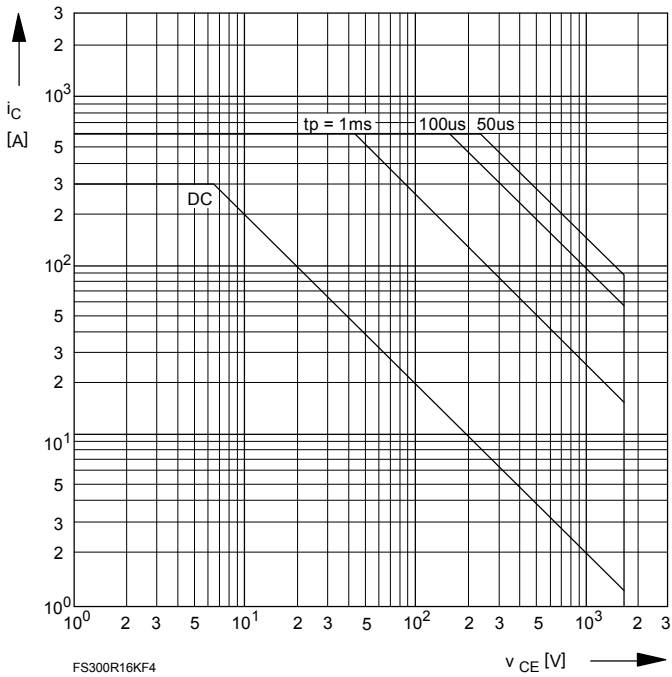
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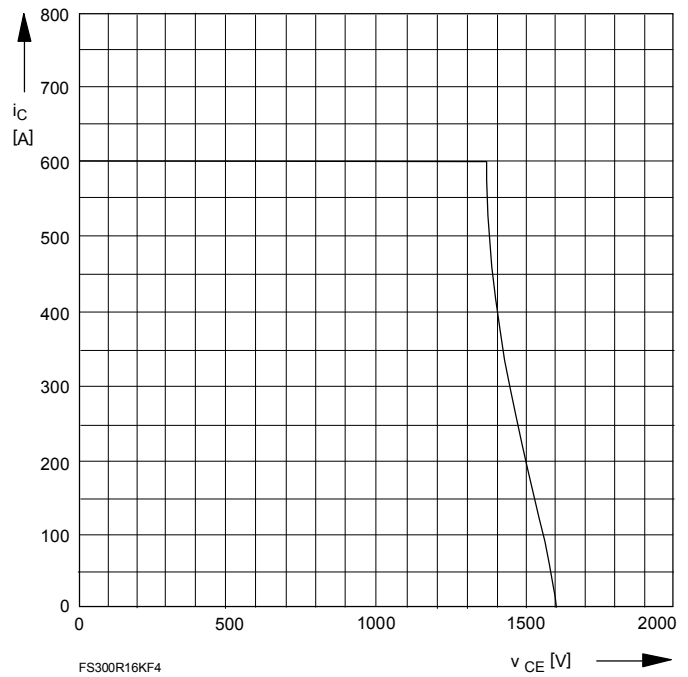
Bild/Fig. 1  
 Kollektor-Emitter-Spannung im Sättigungsbereich (typisch)  
 Collector-emitter-voltage in saturation region (typical)  
 $t_{vj} = 25^\circ\text{C}$



Bild/Fig. 2  
 Übertragungscharakteristik (typisch)  
 Transfer characteristic (typical)  
 $V_{CE} = 20$  V

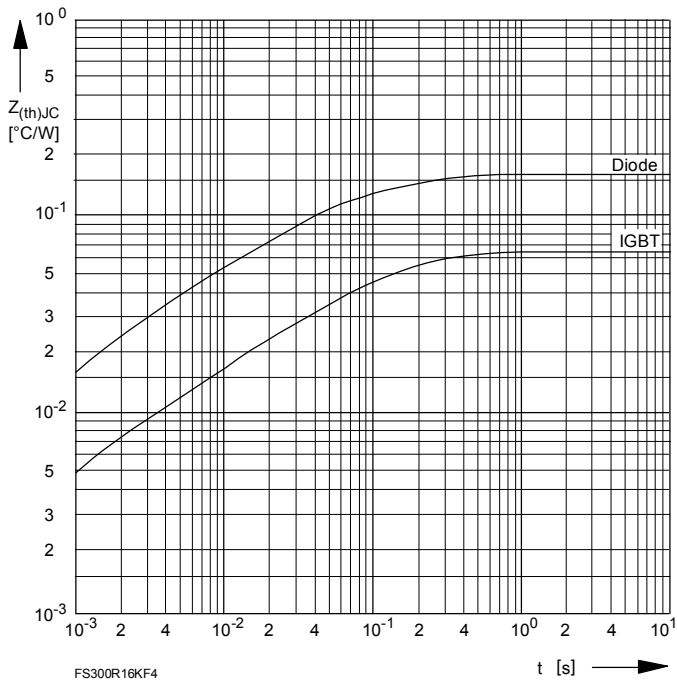


Bild/Fig. 3  
 Vorwärts-Arbeitsbereich (nicht periodisch)  
 Forward biased safe operating area (non repetitive)  
 $t_{vj} = 150^\circ\text{C}$ ,  $t_c = 25^\circ\text{C}$



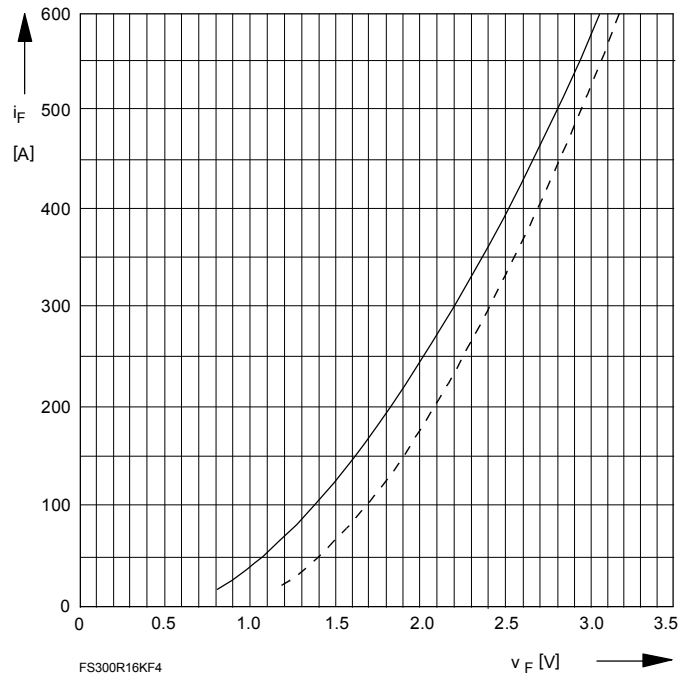
Bild/Fig. 4  
 Rückwärts-Arbeitsbereich  
 Reverse biased safe operating area  
 $t_{vj} = 125^\circ\text{C}$ ,  $v_{LF} = v_{LR} = 15$  V,  $R_G = 6,8 \Omega$

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Bild/Fig. 5  
 Transienter innerer Wärmewiderstand je Zweig (DC)  
 Transient thermal impedance per arm (DC)



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Bild/Fig. 6  
 Durchlaßkennlinie der Inversdiode (typisch)  
 Forward characteristic of the inverse diode (typical)  
 .....  $t_{vj} = 25^{\circ}C$   
 —  $t_{vj} = 125^{\circ}C$

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